DONGGUAN NANJING ELECTRONICS LTD.,

TO-247-3 Silicon Carbide Schottky Diode

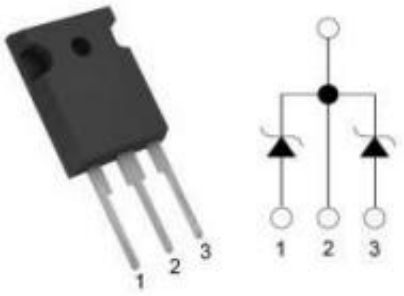
NJ40PD065B SiC Diode 650V, 40A, 88nC

General Description

This product family offers state of the art performance. It is designed for high frequency applications here high efficiency and high reliability are required.

Features

- Zero Forward/Reverse Recovery Current
- High Blocking Voltage
- High Frequency Operation
- Positive Temperature Coefficient on VF
- Temperature Independent Switching Behavior
- High surge current capability



TO-247-3
Pin definition

Applications

- Servo Drives
- Solar / Wind Inverters
- AC/DC converters
- DC/DC converters
- Uninterruptable power supplies

Benefits

- Higher System Efficiency
- Parallel Device Convenience without thermal runaway
- Higher Temperature Application
- No Switching loss
- Hard Switching & Higher Reliability
- Environmental Protection

Key performance parameters

Type	V_R	I_F T_C=150℃	Q_C
NJ40PD065B	650V	40A**	88nC**

Caution: This device is sensitive to electrostatic discharge .Users should follow ESD handing procedures.

Maximum Ratings

T_C=25℃, unless otherwise specified

Parameter	Symbol	Value	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	650	V
Peak Reverse Surge Voltage	V_{RSM}	650	V
DC Blocking Voltage	V_R	650	V

Maximum Ratings

T_C=25℃, unless otherwise specified

Parameter	Symbol	Value	Unit
Continuous Forward Current: (per leg / per device) T_C = 25°C T_C = 135°C T_C = 150°C	I_F	46/92 24/48 20/40	A
Non Repetitive Forward Surge Current：* T_C = 25°C, tp =10ms, Half Sine Pulse T_C = 110°C, tp =10ms, Half Sine Pulse	I_{FSM}	135 120	A
Repetitive peak Forward Surge Current: * Freq = 0.1Hz, 100 cycles T_C = 25°C, tp=10ms, Half Sine Pulse T_C = 110°C, tp=10ms, Half Sine Pulse	I_{FRM}	110 110	A
Total power dissipation (per leg / per device): T_C = 25°C	P_D	150/300	W
Operating Junction Temperature	T_j	-55 to 175	°C
Storage Temperature	T_{stg}	-55 to 175	°C

Note : * Per leg ** Per device

Thermal Resistance

Parameter	Symbol	Typ.	Max	Unit
Thermal resistance,(per device)	R_{thJC}	0.5		°C/W

Electrical Characteristic

T_C =25°C, unless otherwise specified

Parameter	Symbol	Value			Unit	Test Condition
		Min.	Typ.	Max.		
DC Blocking Voltage *	V_{DC}	650			V	T_j = 25°C
Forward Voltage *	V_F		1.5 1.6 1.7	1.8	V	I_F = 20A T_j = 25°C T_J = 125°C T_j = 175°C
Reverse Current *	I_R		10 50 150	80	uA	V_R = 650V T_j = 25°C T_J = 125°C Tj = 175°C
Total Capacitance Charge *	Q_C		52		nC	V_R = 400V T_J = 25°C
Total Capacitance *	C		900 118 90		pF	V_R = 1V V_R = 200V V_R = 400V T_J = 25°C Freq = 1MHz

Note: This is a majority carrier diode, so there is no reverse recovery charge

Characteristics Curves

Figure 1. Forward Characteristics

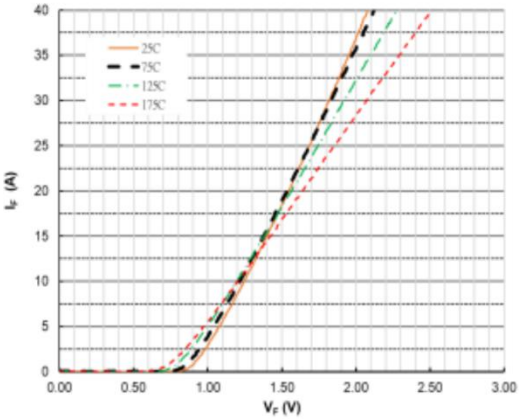


Figure 2. Forward Characteristics

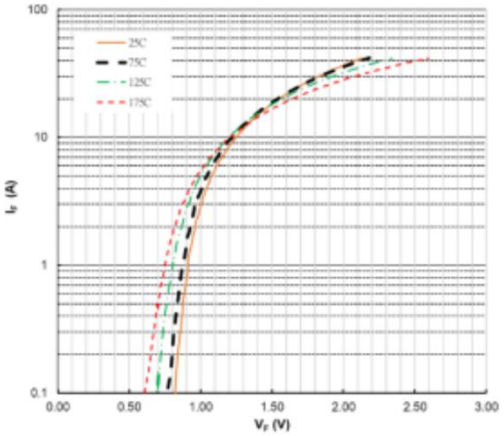


Figure 3. Reverse Characteristics

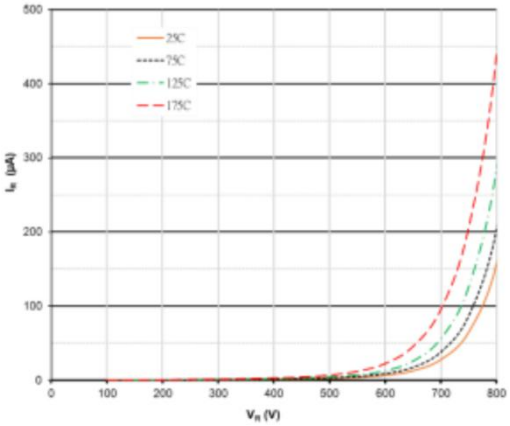


Figure 4. Power Derating

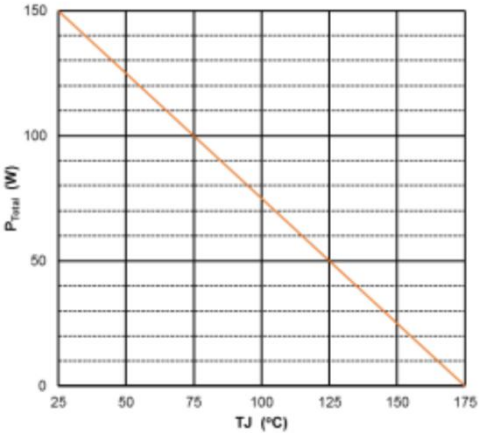


Figure 5. Capacitance vs Reverse Voltage

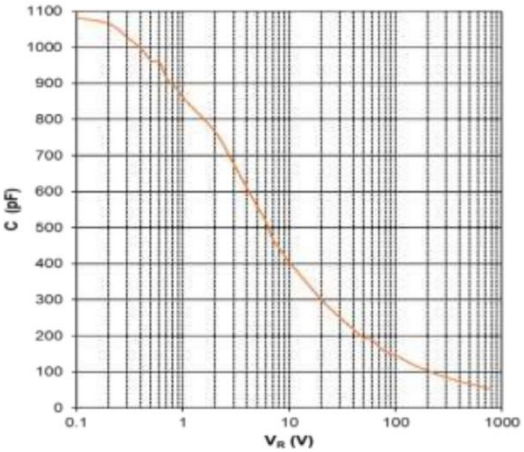
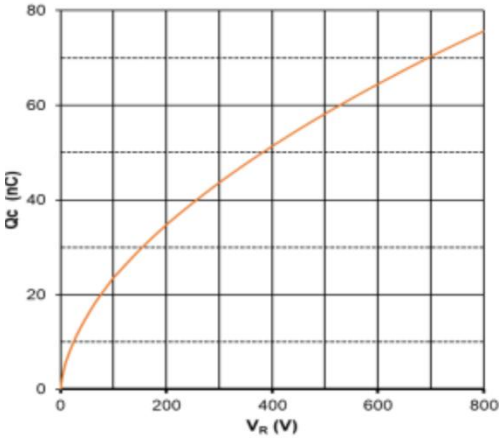
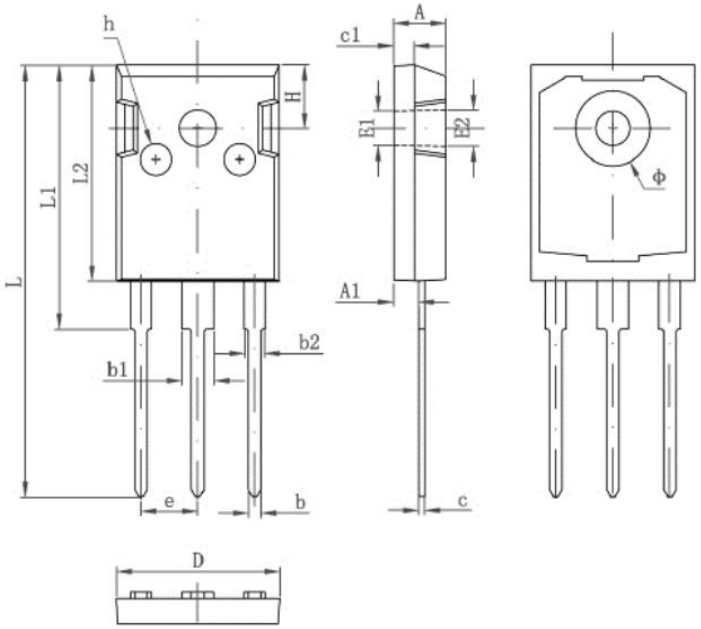


Figure 6. Recovery Charge vs Reverse Voltage



Package Outline:TO-247-3



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	4.850	5.150	0.191	0.200
A1	2.200	2.600	0.087	0.102
b	1.000	1.400	0.039	0.055
b1	2.800	3.200	0.110	0.126
b2	1.800	2.200	0.071	0.087
c	0.500	0.700	0.020	0.028
c1	1.900	2.100	0.075	0.083
D	15.450	15.750	0.608	0.620
E1	3.500 REF		0.138 REF	
E2	3.600 REF		0.142 REF	
L	40.900	41.300	1.610	1.626
L1	24.800	25.100	0.976	0.988
L2	20.300	20.600	0.799	0.811
Φ	7.100	7.300	0.280	0.287
e	5.450 TYP		0.215 TYP	
H	5.980 REF		0.235 REF	
h	0.000	0.300	0.000	0.012